

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	Wafer Vendor
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	410.50 +/- 11.00 μ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00 μ m	Guaranteed by Process
	7.0	Bow	<100.00 μ m	ADE 100%, SEMI MF1530
	8.0	Warp	<100.00 μ m	ADE 100%, SEMI MF1530
	9.0	Edge Exclusion	5mm	
HandleSilicon	10.0	Handle Growth Method	CZ	Wafer Vendor
	11.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	12.0	Handle Thickness	400.00 +/- 10.00 μ m	ADE, 100%
	13.0	Handle Doping Type	N	Wafer Vendor
	14.0	Handle Dopant	Phosphorus	Wafer Vendor
	15.0	Handle Resistivity	1~5 Ohm-cm	Wafer Vendor
	16.0	Backside Finish	Polished with Oxide, and Laser mark	Wafer Vendor
BuriedOxide	17.0	Oxide Type	Thermal	Guaranteed by process
	18.0	Oxide Thickness	5,000.00 +/- 250.00 A	Nanospec 5pt, 4% sample
	19.0	Oxide formed on	Handle or/and Device wafer	Guaranteed by process
DeviceSilicon	20.0	Device Growth Method	CZ	Wafer Vendor
	21.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	22.0	Nominal Thickness	10.00 +/- 0.50 μ m	Filmetrics, 100% 9-Pt (note3)
	23.0	Device Doping Type	N	Wafer Vendor
	24.0	Device Dopant	Any	Wafer Vendor
	25.0	Device Resistivity	0.050~0.060 Ohmcm	Wafer Vendor
	26.0	Voids	0	Bright Light, 100% (note2)
	27.0	Scratches	0	Bright Light, 100% (note2)

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information